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APPLICANT: B. Martinez-Tovar et al

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TITLE: TITANIUM SEMICONDUCTOR BRIDGE

:

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RESPONSE TO OFFICE ACTION

Commissioner for Patents
Box RCE
Washington, DC 20231

Jan 25 2002
RECEIVED

FEB 27 2002

GROUP 3600

Dear Sir:

This paper is responsive to the office action mailed September 25, 2001 in the captioned application.

AMENDMENTS

In The Specification

Amend the paragraph at page 2, lines 6-14 to read as follows.

In accordance with the present invention there is provided a titanium semiconductor bridge device comprising a substrate and an electrical bridge structure disposed on the substrate. The bridge structure comprises a layer of a material having a negative coefficient of electrical conductivity at temperatures above ambient temperature and having disposed thereover a layer consisting essentially of titanium, the bridge structure comprising a bridge section extending between and connecting spaced-apart pad sections, each pad section being of larger area than the bridge section. A pair of electrically conductive lands each overlies a respective one of the pad sections and is spaced apart from the other land to leave the bridge section exposed.

Amend the paragraph at page 2, line 31 through page 3, line 3 as follows.